

MCI100N65E3A2

V_{CE}	$I_{c\ nom}$
650V	100A

DESCRIPTION

MCI100N65E3A2 modules using JSCJ's third generation IGBT technology which has advanced Trench and FS(Field Stop) Structure, have very low Collector Emitter Saturation Voltage, can easy to use in drives and inverters.

A2



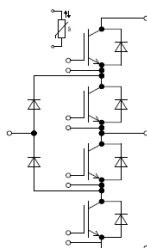
Features

- Low $V_{ce(sat)}$ and positive temperature coefficient
- Low switching loss
- Standard housing
- Solder contact technology

● Application

- APF
- Power Storage
- Solar

EQUIVALENT CIRCUIT



Order Code	Package	Marking	Parking
MCI100N65E3A2	A2	MCI100N65E3A2	Module



JIANGSU CHANGJING ELECTRONICS TECHNOLOGY CO., LTD.

IGBT Discrets & Modules

感谢您的支持，如需要完整规格书，请联系：<igbt.list@jscj-elec.com>，谢谢！

Thank you for your support. If you need a complete **datasheet**, please contact:

<igbt.list@jscj-elec.com>. Thank you!